

Exercise Circ24

Consider a CMOS fabrication process with the following process parameters:

$$k_n' = \mu_n C_{ox} = 150 \mu A/V^2, \quad k_p' = \mu_p C_{ox} = 75 \mu A/V^2,$$

$$V_{th,n} = |V_{th,p}| = 0.55 \text{ V},$$

$L_{min} = 0.5 \mu m$ (minimum allowed channel length, for both N-channel and P-channel transistors),

$C_{ox} = 2.5 \text{ fF}/\mu m^2$ (gate oxide capacitance per unit area),

$C_{ov} = 0.20 \text{ fF}/\mu m$ (gate overlap capacitance per unit length per each side, including both overlap and fringing effects),

$t_{ox} = 12 \text{ nm}$ (gate oxide thickness).

Consider an elementary inverter whose transistors have the following sizes:

n -channel transistor: W_n (channel width) = $2 \mu m$; L_n (channel length) = L_{min} ;

p -channel transistor: W_p (channel width) = $4 \mu m$; L_p (channel length) = L_{min} .

The used fabrication technology and the layout are such that, for each transistor, the drain capacitance and the source capacitance are equal to 20% and 25%, respectively, of the overall gate capacitance, whereas the capacitances associated to interconnections are negligible.

Supply voltage V_{DD} is equal to 3 V.

The cascade of two suitably designed inverters has to be included, as a buffer, between the above elementary inverter and a load capacitor C_L equal to 10 pF, as shown in Fig. 1.

The candidate is asked to:

- design the two inverters 1 and 2 so as to adequately limit the overall delay time from a transition of input signal IN and the ensuing transition of output signal OUT;
- calculate the delay time from a transition of input signal IN and the ensuing transition of output signal OUT when the buffer as designed from item a) is used;
- assume now that a series inductance $L = 2 \text{ nH}$ and a series resistance $R = 2 \Omega$ are present between the source terminal of the pull-down transistor (M_D) of the last stage of the buffer designed as from item a) and ground (as shown in Fig. 2); the candidate is asked to estimate the noise that arises at the source terminal of transistor M_D due to a transition 1/0 of output signal OUT, which takes place as a consequence of a transition 0/1 of input signal IN in Fig. 1.

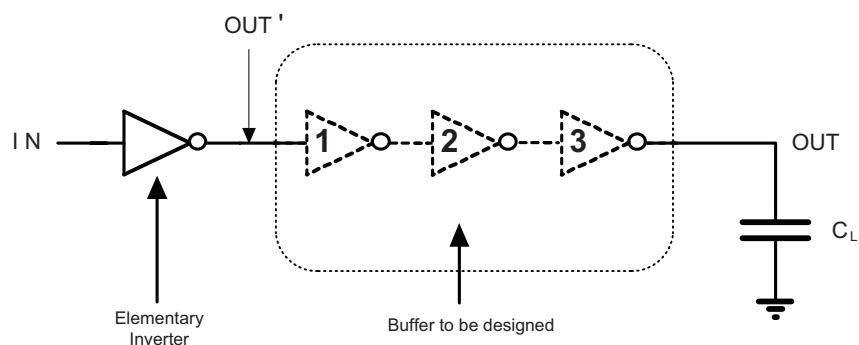


Figura 1

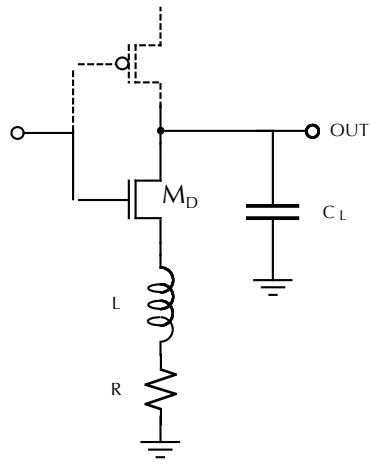


Figura 2